

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

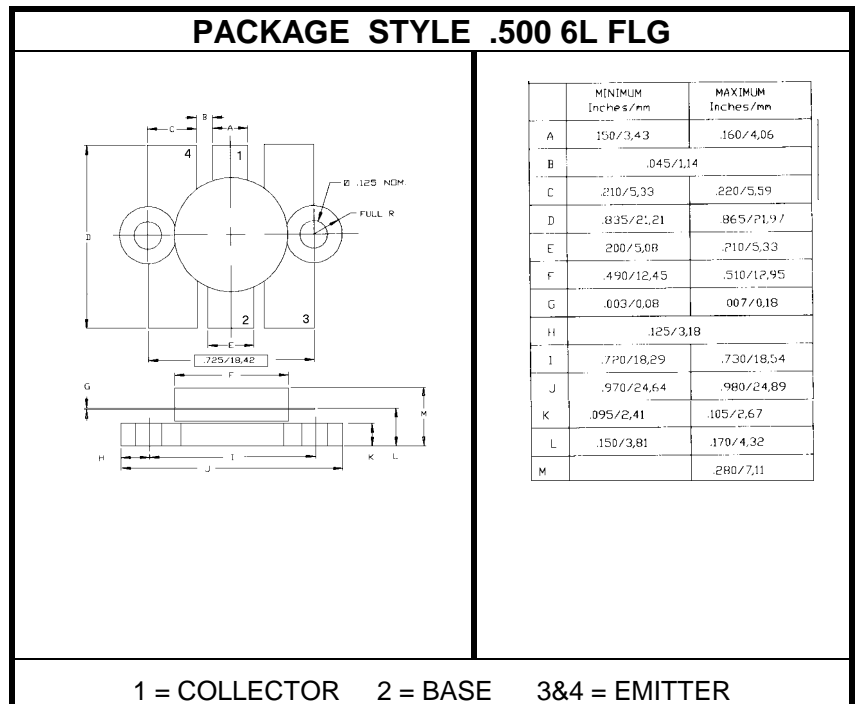
The ASI BM100-28 is Designed for high power VHF Applications up to 200 MHz.

## FEATURES:

- Common Emitter
- $P_G = 8.5$  dB at 20 W/175 MHz
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	20 A
$V_{CEO}$	33 V
$V_{CES}$	65 V
$V_{EBO}$	4.0 V
$P_{DISS}$	270 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	$0.65^\circ\text{C/W}$



## CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA		33			V
$BV_{CES}$	$I_C = 100$ mA		65			V
$BV_{EBO}$	$I_E = 5.0$ mA		4.0			V
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 1.0$ A	10			---
$C_{CB}$	$V_{VB} = 28$ V	$f = 1.0$ MHz		200		pF
$P_G$ $\eta_C$	$V_{CC} = 28$ V	$P_{OUT} = 100$ W	8.5	60		dB %